

FIG. 1

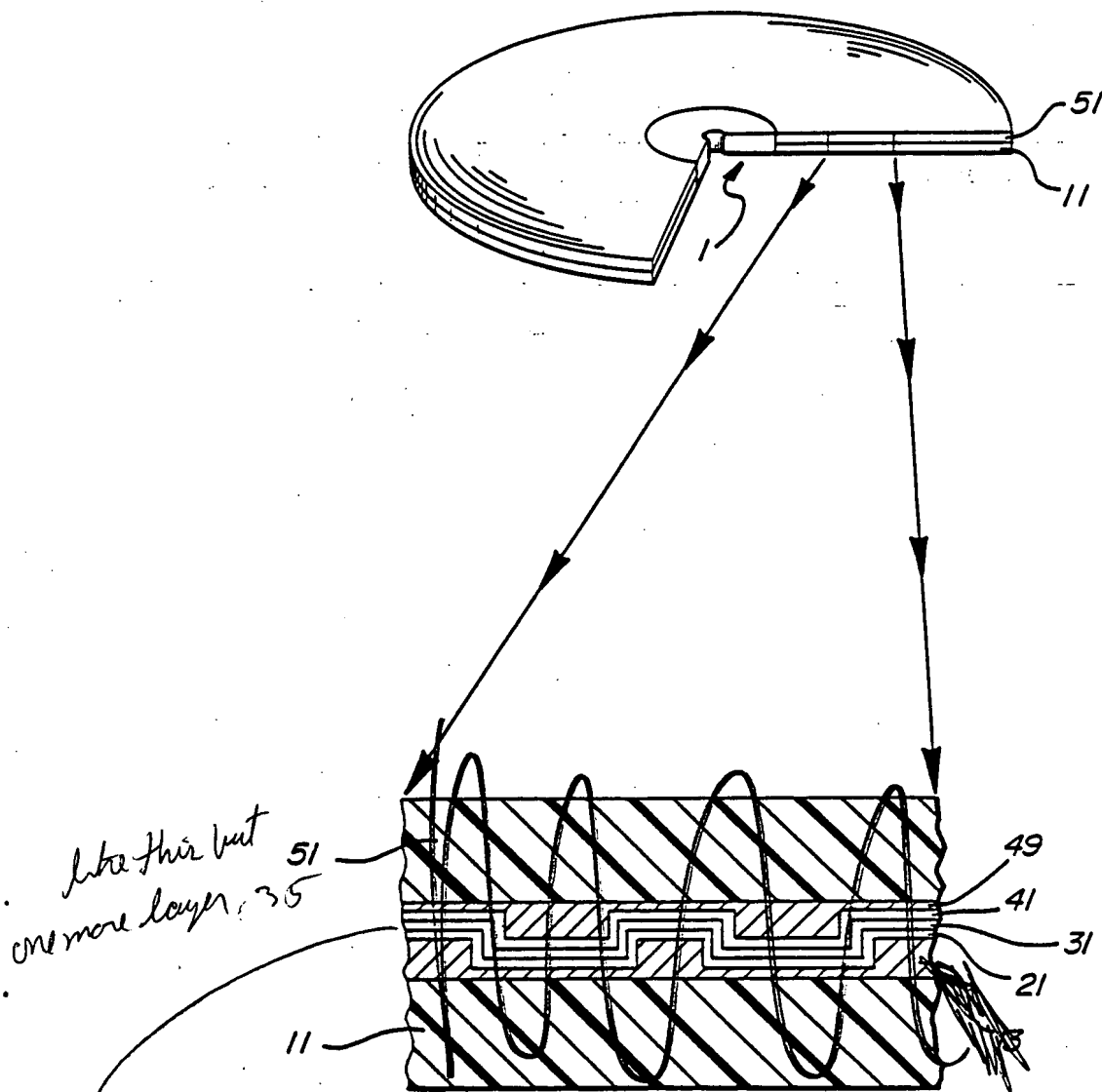
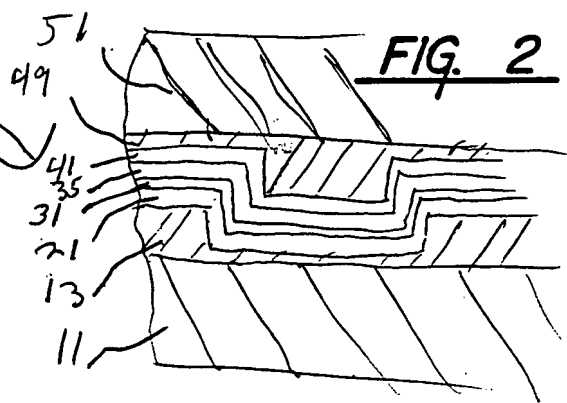


FIG. 2



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# WRITE ONCE SEQUENCE

SAMPLE NO: E-1048

DATE: 3/21/89

Te536e37Sb10/Sb

CRYSTALLIZATION PULSE WIDTH:

.025US

.05 US

.075US

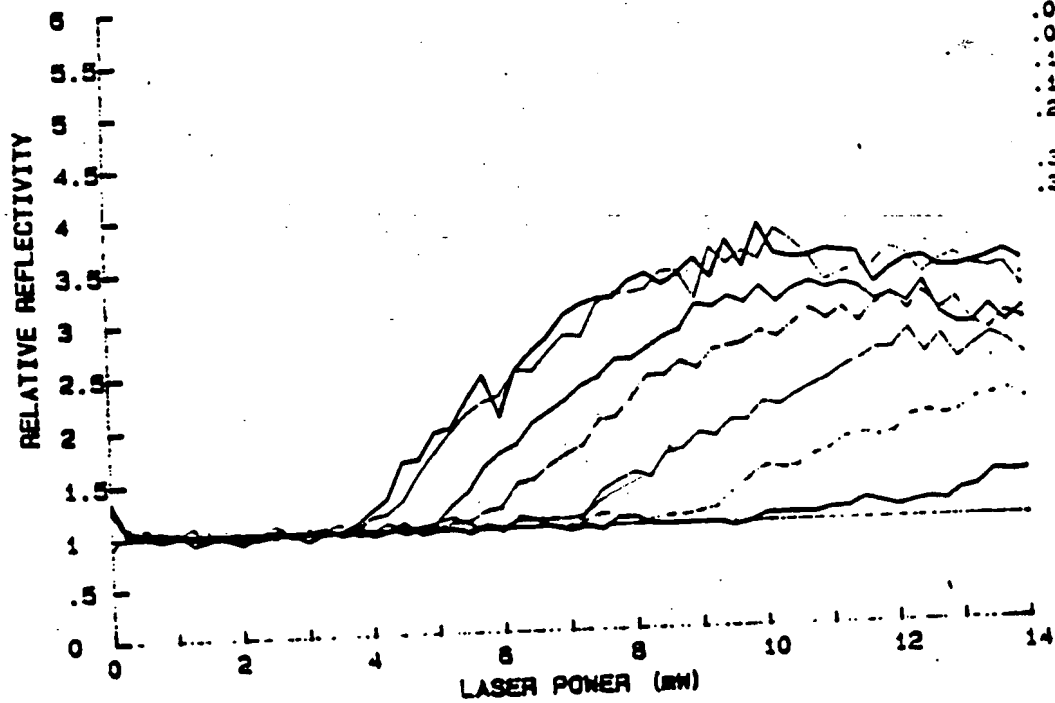
.10 US

.15 US

.20 US

.30 US

.35 US



3  
Figure ~~14~~

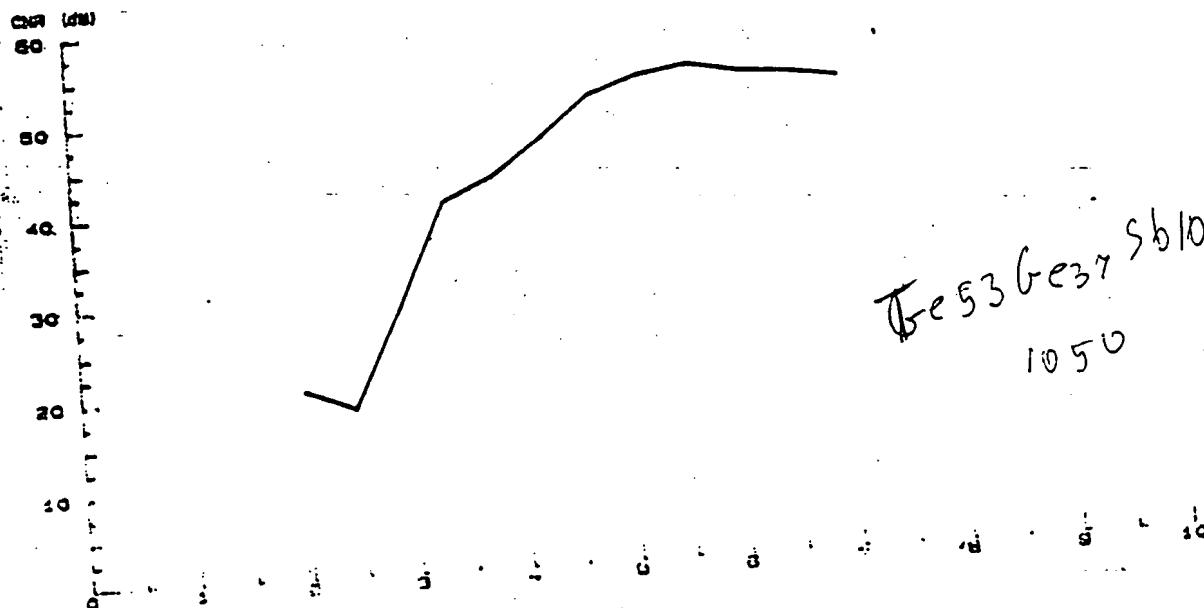
# CARRIER TO NOISE RATIO V.S RECORD POWER

E-1050  
 Te: Ge: Sb/Sb  
 : unsealed disc  
 DATE : 24 Mar 1989

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RECORD FREQUENCY: 3.86 MHz

INITIALIZED 0 CYCLES 10 M, S



Te 53 Ge 37 Sb 10  
 1050

4  
Figure 20

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CARRIER-TO-NOISE RATIO  
1.5  
RECORD FREQUENCY

SAMPLE NO : E-1050  
DESCRIPTION : Te: Ge: Sb/Sb  
: unsealed disc  
DATE : 24 Mar 1989

RECORD POWER: 5.5 mW

INITIALIZED 0 CYCLES 1TH 10 W.S

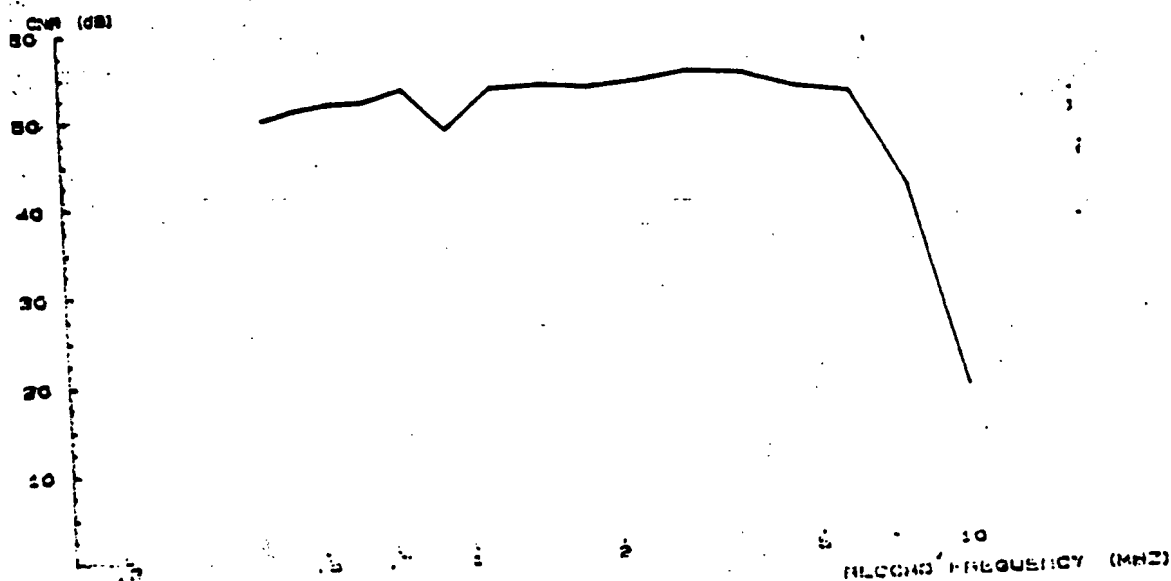


Figure 24

## Rate vs Time

Te Ge Sb alloy source (50:41:9)

4/12/89

E-1072 520 C

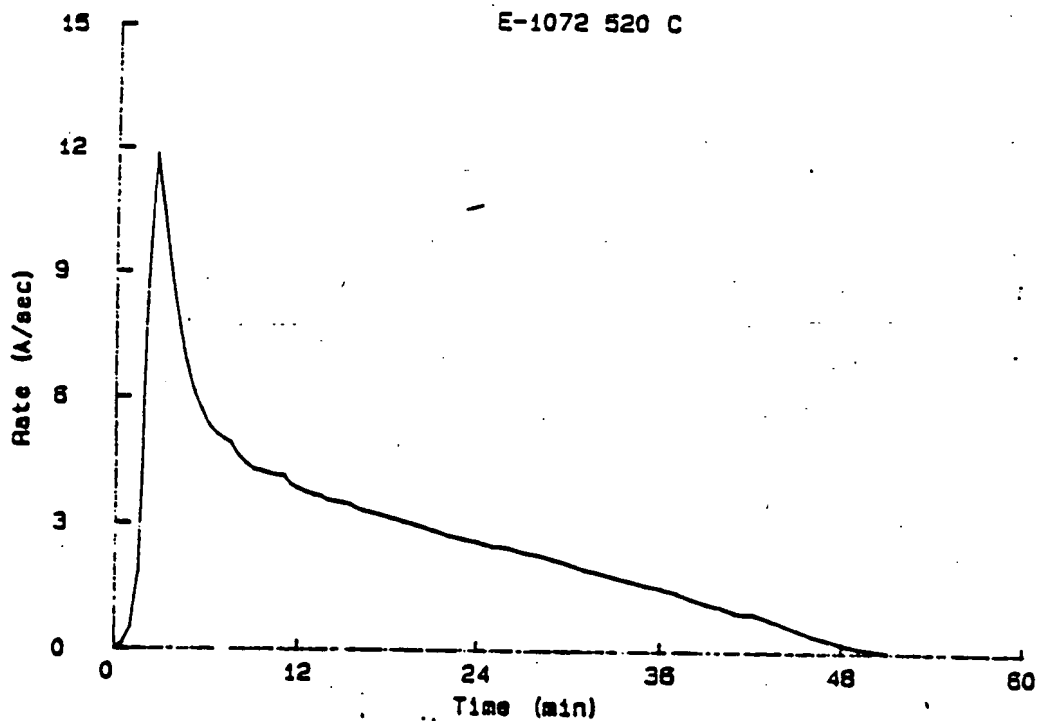


Fig 6

Figure 32

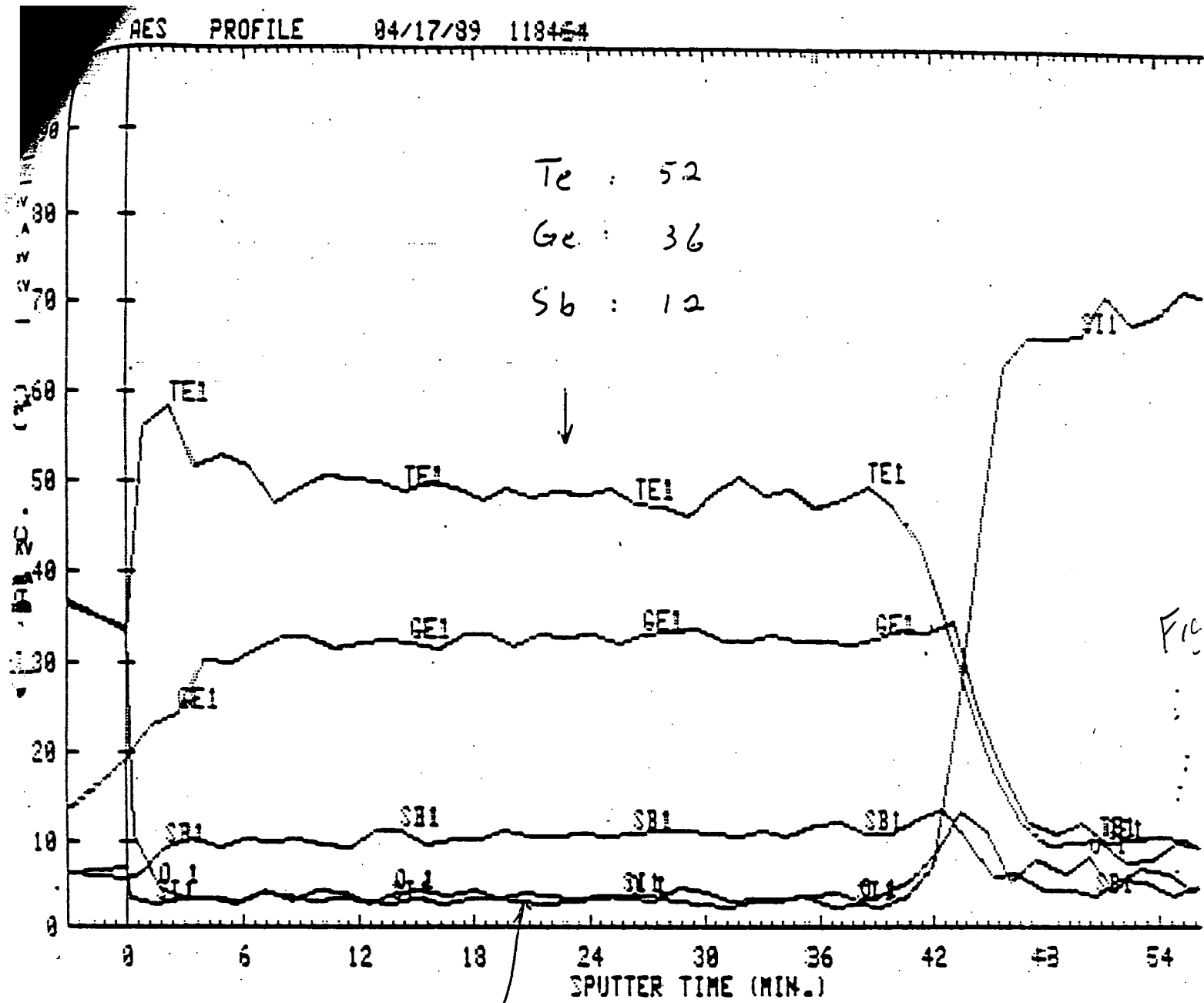


Figure 33

657170

AES

E1370

1184

OBJECT #

1.524 A

1.524 A

1.524 A

1.524 A

1.524 A

1.524 A

1.524 A

1.524 A

1.524 A

1.524 A

1.524 A

1.524 A

1.524 A

1.524 A

1.524 A

1.524 A

1.524 A

1.524 A

1.524 A

1.524 A

1.524 A

1.524 A

1.524 A

1.524 A

1.524 A

1.524 A

1.524 A

1.524 A

1.524 A

1.524 A

1.524 A

1.524 A

1.524 A

1.524 A

1.524 A

1.524 A

1.524 A

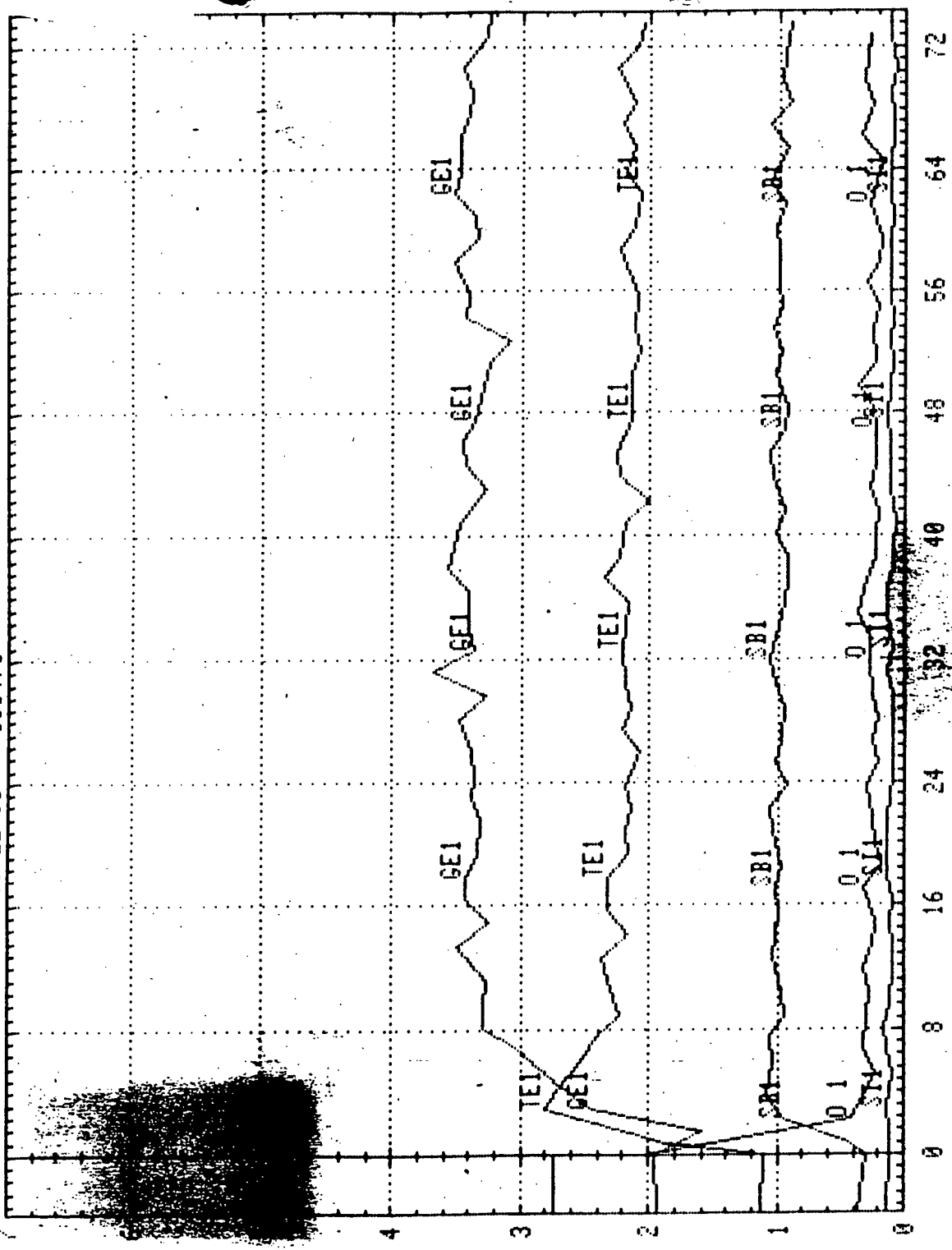
1.524 A

1.524 A

08/22/90

118473

RES PROFILE



SPUTTER TIME (MIN.)

Fig 8

SPUTTER RATE: 5.0 g/WRT 14.05

PAR ~ 6.5 mA

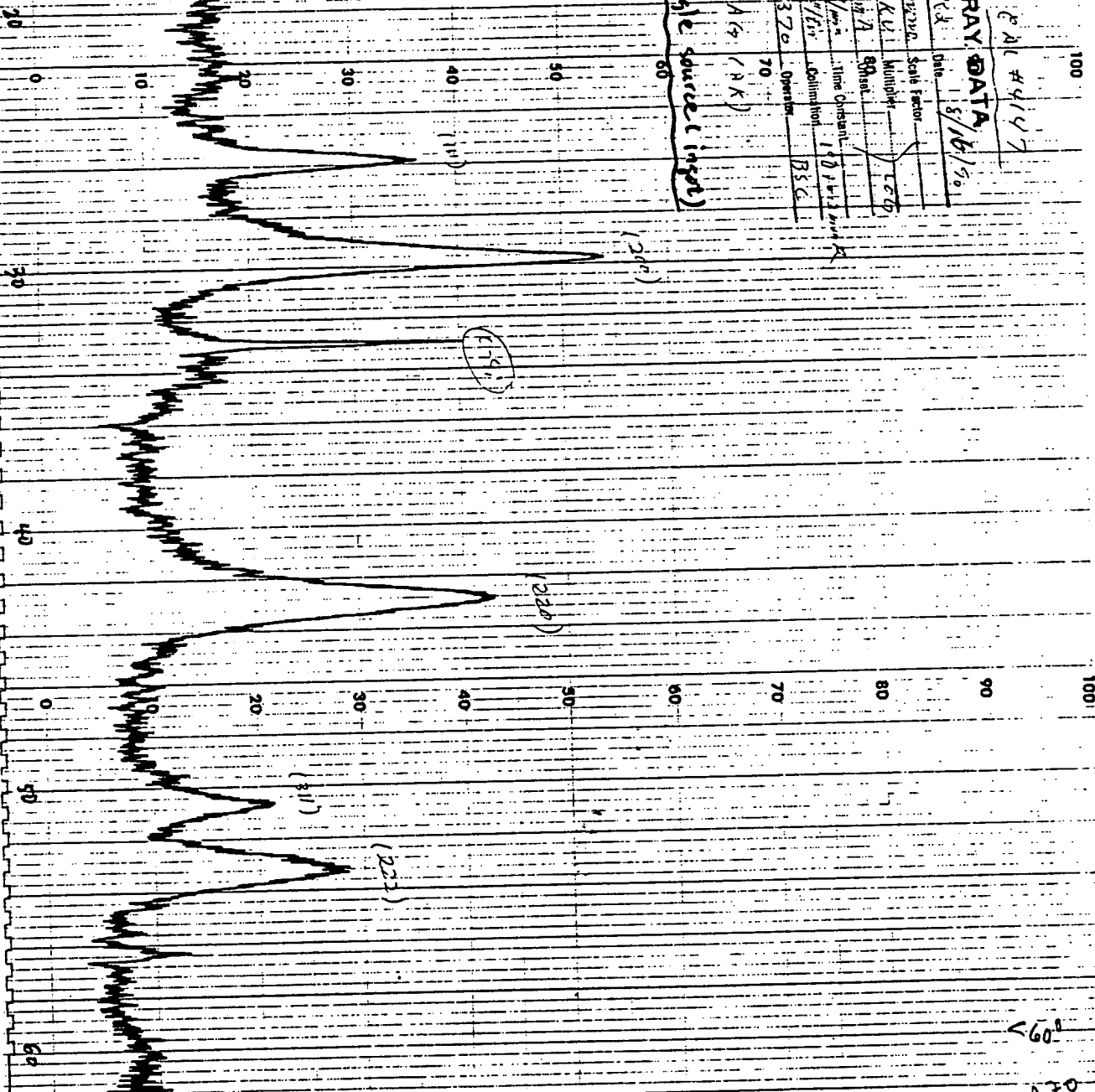
B-TAG

TE51 Ge40 Sb9

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Tube Cu/K $\alpha$  Date 6/16/90  
 Filter C-115230C Scale factor 1.000  
 Voltage 4.5 kV Multiplier 1.000  
 Current 8.0 mA Time constant 1.000  
 Scan Speed 3.0 deg/min Collimation 1.000  
 Chart Speed 3.0 deg/min Operation BSC  
 Sample # 1370

( $\beta$ -7A (9.1 Å))  
 Single source (input)



< 60°  
 E1370  
 P-TAB  
 609  
 204 301

Fig 9